

**REMARKS**

This application has been carefully reviewed in light of the Office Action mailed December 21, 2006. Claims 1-18 are pending and Claims 15-18 are allowed. The Office Action rejects Claims 1-14. Applicant respectfully requests reconsideration and favorable action of all pending claims in view of the following remarks.

**Allowable Subject Matter**

Applicants note with appreciation the allowance of Claims 15-18.

**Section 102 and 103 Rejections**

Claims 1, 4-5, 7 are rejected under 35 U.S.C. 102(b) as being anticipated by U.S. Patent No. 4,646,424 to Parks et al. ("*Parks*"). Claims 2-3 are rejected under 35 U.S.C. 103(a) as being unpatentable over *Parks* in view of U.S. Patent Application Publication No. 2004/0053505 A1 by Chinn et al ("*Chinn*"). Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over *Parks* in view of U.S. Patent No. 6,472,315 to Nguyen et al ("*Nguyen*"). Claims 8, 11-12, 14 are rejected under 35 U.S.C. 103(a) as being unpatentable over *Parks* in view of U.S. Patent Application Publication No. 2004/0063595 A1 by Park et al. ("*Park*") Claims 9-1 are rejected under 35 U.S.C. 103(a) as being unpatentable over *Parks* in view of *Park* and further in view of *Chinn*. Claim 13 is rejected under 35 U.S.C. 103(a) as being unpatentable over *Parks* in view of *Park* and further in view of *Nguyen*. Applicant respectfully traverses this rejection for at least the reasons stated below.

Claim 1 is allowable at least because *Parks* fails to disclose, teach, or suggest, "providing a wafer having an etched patterned layer and an overlying mask pattern resist" and "cleaning the wafer with a develop solution." The Office Action incorrectly states that *Parks* teaches this limitation by "cleaning the wafer with water (col 6, lines 18-21)." Applicant respectfully submits that the Office Action has mischaracterized the teachings of *Parks* at least because the water clean in *Parks* (col 6, lines 18-21) is not applied to a wafer "after an etch of an underlying patterned layer that is supported by a spacer layer," as recited in Claim 1. In particular, the water clean in *Parks* occurs prior to patterning and plasma etching the titanium layer (col. 6, lines 20-22 and 30-32), or any other layer, and therefore fails to disclose, teach, or suggest, a method of "removing pattern resist that remains after an

etch,” as recited in Claim 1. For at least these reasons, Claim 1 is allowable, as are all claims depending therefrom. Favorable action is requested.

Claim 8 is allowable at least for analogous reasons. In particular, Claim 8 is allowable at least because *Parks* fails to disclose, teach, or suggest, “cleaning the resist material and remaining material for the patterned layer with a develop solution **after said etching step**.” The Office Action again incorrectly relies on the water clean of *Parks* (col 6, lines 18-20), which is performed **before** the plasma etch of the titanium layer (col 6, lines 30-32). For at least this reason, Claim 8 is allowable, as are all claims depending therefrom. Favorable action is requested.

CONCLUSION

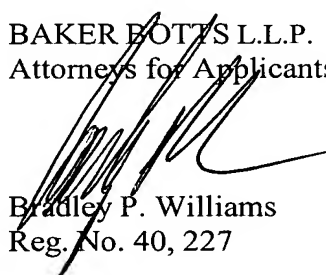
Applicant has made an earnest attempt to place this case in condition for allowance. For at least the foregoing reasons, Applicant respectfully requests full allowance of all pending claims.

If the Examiner believes that a telephone conference would advance prosecution of this Application in any manner, the Examiner is invited to contact the undersigned Attorney for Applicant at the Examiner's convenience.

Applicant believes that no fee is due. However, the Commissioner is hereby authorized to charge any additional fees or credit any overpayments to Deposit Account No. 02-0384 of Baker Botts L.L.P.

Respectfully submitted,

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